PSMN2R0-60PSR

N-channel 60 V, 2.2 mΩ standard level MOSFET in TO-220 using Trench Technology

25 June 2014 **Product data sheet**

1. General description

Standard level gate drive N-channel enhancement mode MOSFET in TO-220 package using advanced TrenchMOS technology. This product has been designed and qualified to 175 °C for use in a wide range of industrial, communications and Power Supply Equipment.

2. Features and benefits

- Low Q_G, Q_{GD} and Q_{OSS} for high system efficiency
- High reliability TO-220 package
- Qualified to 175 °C
- Reflow solderable

3. Applications

- Server and Telecom voltage regulator
- DC-to-DC, POL and System Power
- Motor Control
- Power OR-ing
- Sync Rectifier
- Load switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	60	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; Fig. 2	[1]	-	-	120	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; Fig. 1		-	-	338	W
T_j	junction temperature			-55	-	175	°C
Static characteristics							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 25$ °C; Fig. 12	[2]	-	1.8	2.2	mΩ
		$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 100$ °C; Fig. 12; Fig. 13		-	3	3.5	mΩ

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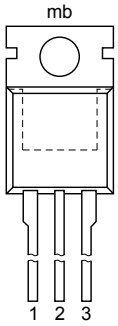
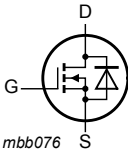
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 75 A; V_{DS} = 30 V; Fig. 14; Fig. 15		-	32	45	nC
$Q_{G(tot)}$	total gate charge			-	137	192	nC
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; Unclamped		-	-	913	mJ

[1] Continuous current limited by package
[2] Measured 3 mm from package.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 **TO-220AB (SOT78)**	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R0-60PSR	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j ≥ 25 °C; T_j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	T_j ≥ 25 °C; T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	60	V

Symbol	Parameter	Conditions		Min	Max	Unit
V_{GS}	gate-source voltage			-20	20	V
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	338	W
I_D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; Fig. 2	[1]	-	120	A
		V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2	[1]	-	120	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C; Fig. 3		-	1135	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	1135	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \leq 60$ V; R_{GS} = 50 Ω; Unclamped		-	913	mJ

[1] Continuous current limited by package

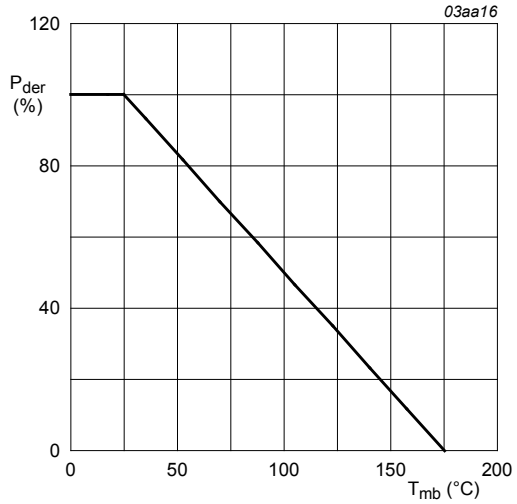


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

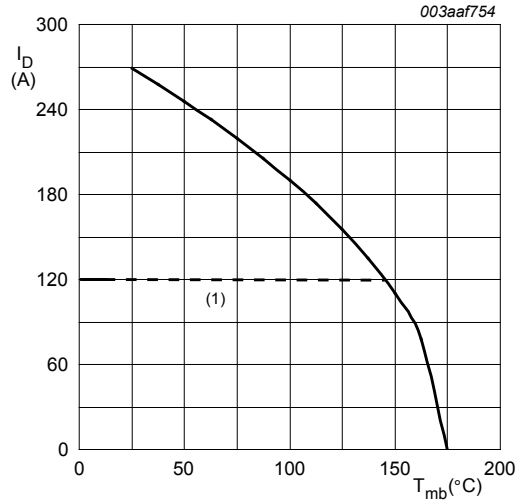


Fig. 2. Continuous drain current as a function of mounting base temperature.

$V_{GS} \geq 10$ V; (1) Capped at 120 A due to package

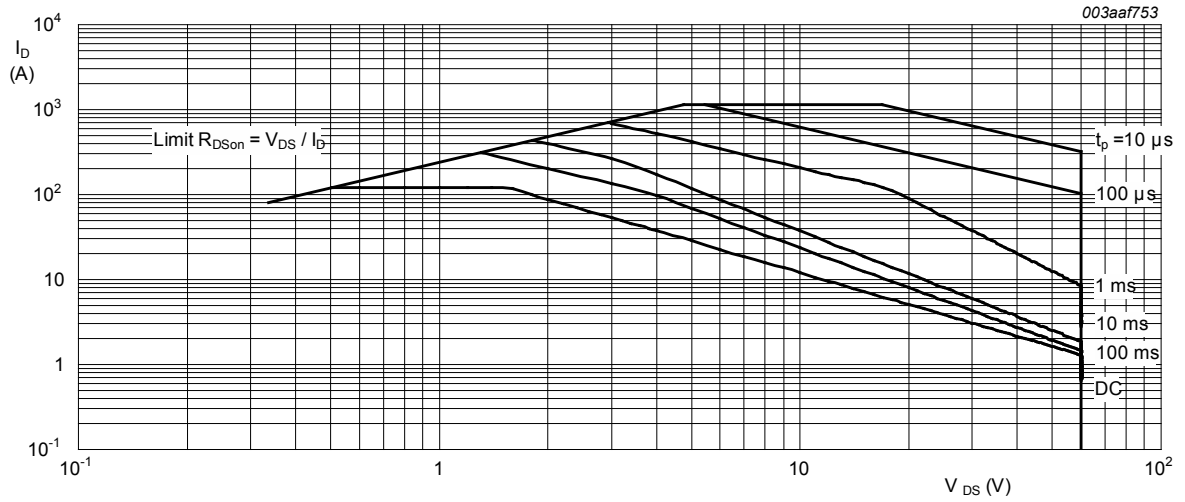


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

T_{mb} = 25 °C; I_{DM} is a single pulse; Capped at 120 A due to package

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4		-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air		-	60	-	K/W

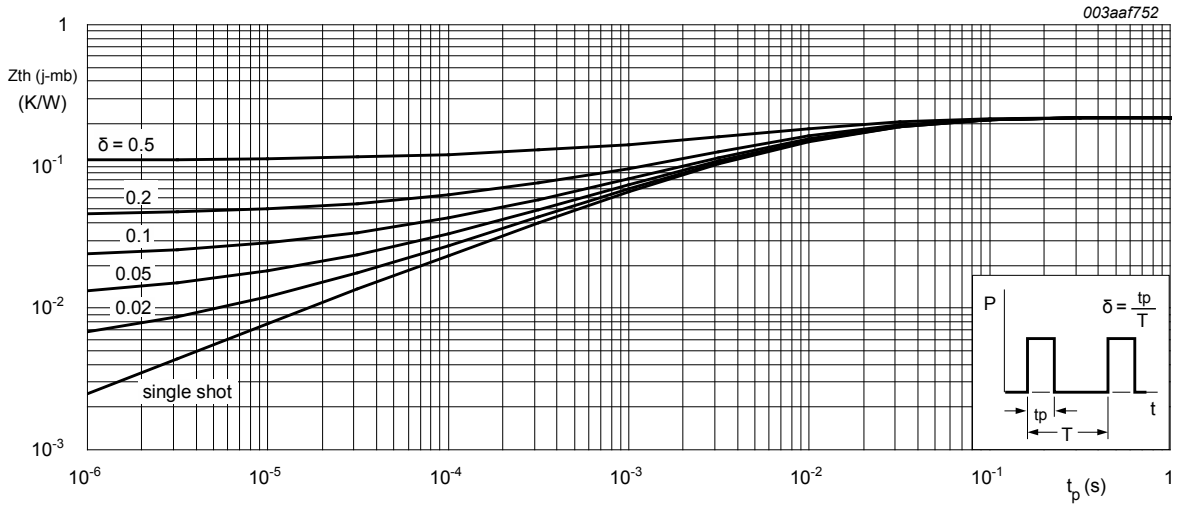


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		54	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 10		1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 11; Fig. 10		2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 10		-	-	4.6	V
I_{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C		-	0.03	10	µA
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 12	[1]	-	1.8	2.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 12; Fig. 13		-	4.3	5.1	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; Fig. 12; Fig. 13		-	3	3.5	mΩ
R_G	gate resistance	f = 1 MHz		0.45	0.9	1.8	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 75 A; V_{DS} = 30 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	137	192	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	129	181	nC
Q_{GS}	gate-source charge	I_D = 75 A; V_{DS} = 30 V; V_{GS} = 10 V		-	48	68	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	I_D = 75 A; V_{DS} = 30 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	29	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	19	-	nC
Q_{GD}	gate-drain charge			-	32	45	nC
$V_{GS(pl)}$	gate-source plateau voltage	V_{DS} = 30 V; Fig. 14; Fig. 15		-	5.7	-	V
C_{iss}	input capacitance	V_{DS} = 30 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 16		-	9997	13500	pF
C_{oss}	output capacitance			-	1210	1640	pF

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C_{rss}	reverse transfer capacitance			-	594	835	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 0.4 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 4.7 Ω; I_D = 75 A		-	42	63	ns
t_r	rise time			-	56	84	ns
$t_{d(off)}$	turn-off delay time			-	115	173	ns
t_f	fall time			-	49	74	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 17		-	0.8	1.2	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 30 V		-	57	75	ns
Q_r	recovered charge	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 30 V		-	80	104	nC

[1] Measured 3 mm from package.

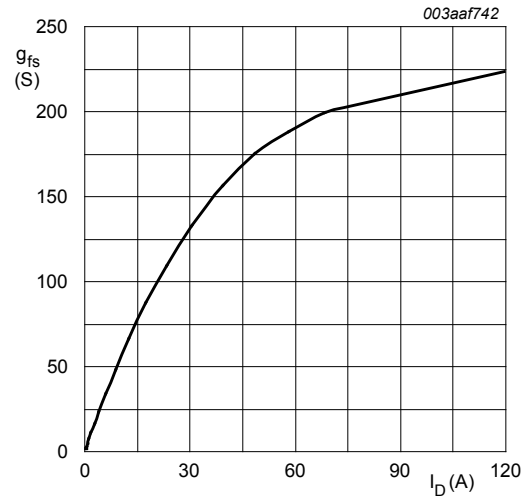


Fig. 5. Forward transconductance as a function of drain current; typical values

$T_j = 25\ °C;\ V_{DS} = 30V$

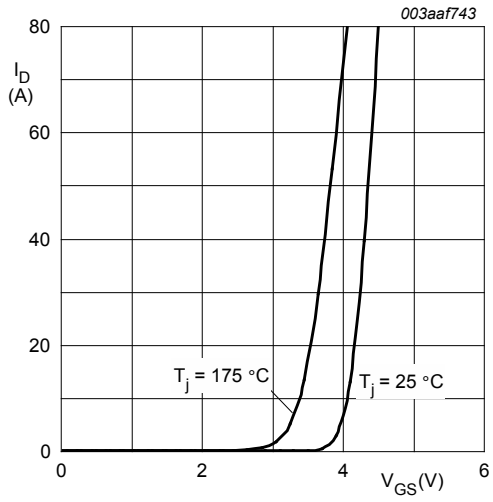


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

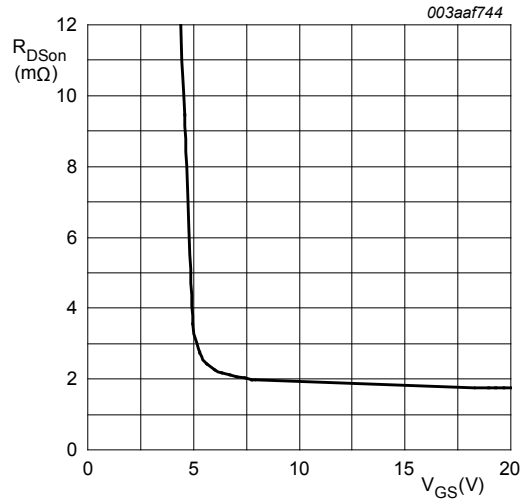


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\ °C; I_D = 25\ A$

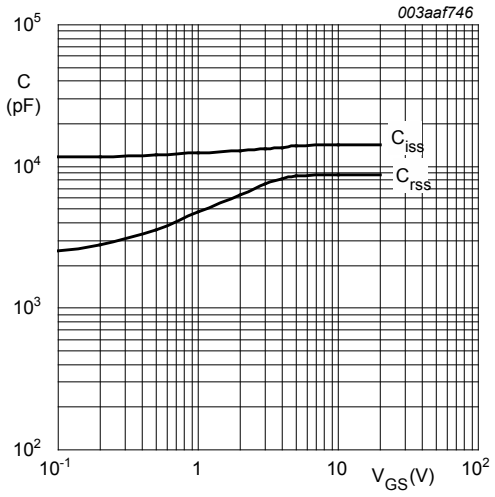


Fig. 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

$V_{DS} = 0\ V; f = 1\ MHz$

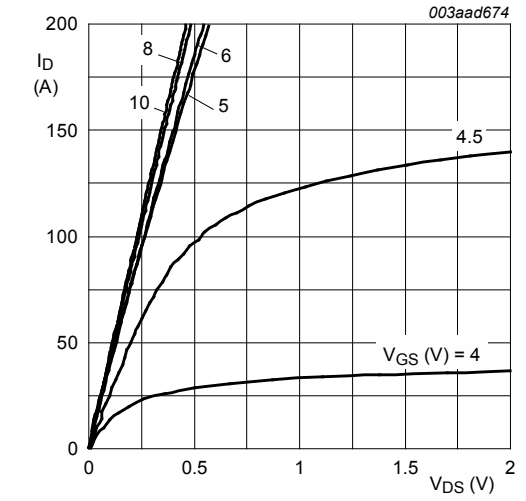


Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\ °C$

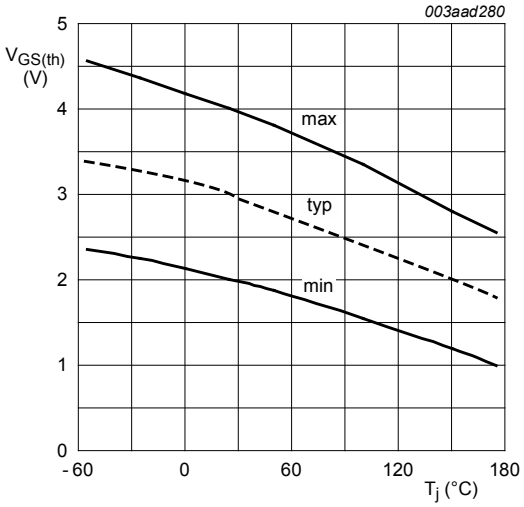


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\ mA; V_{DS} = V_{GS}$

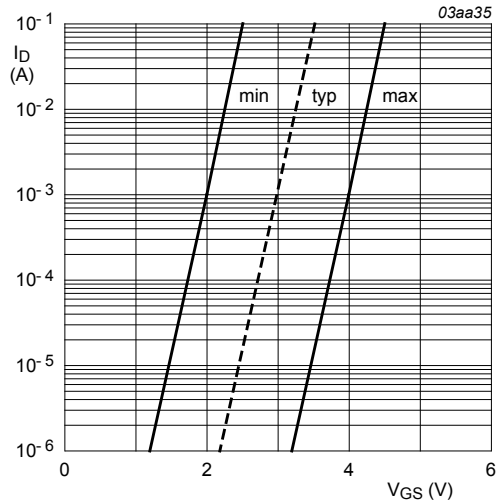


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\,°C; V_{DS} = 5V$

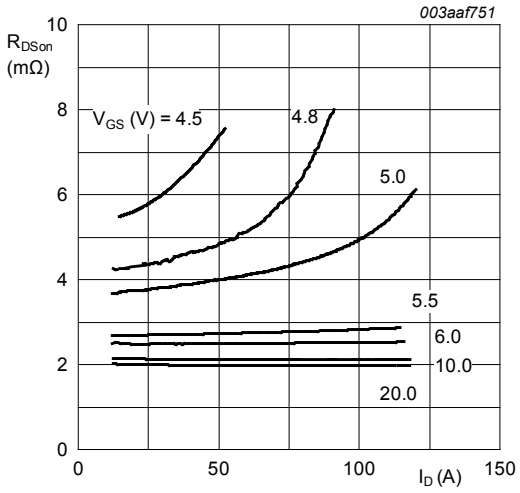


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25\,°C$

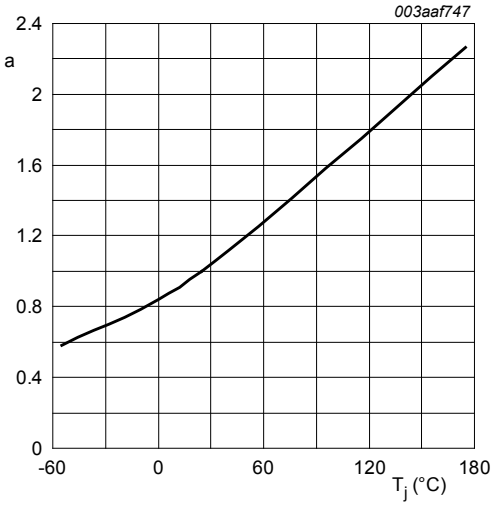


Fig. 13. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\ °C; I_D = 25\ A$

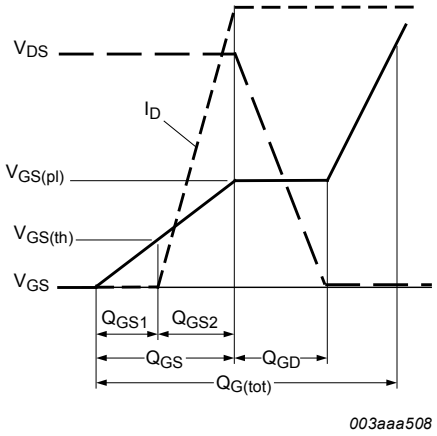


Fig. 14. Gate charge waveform definitions

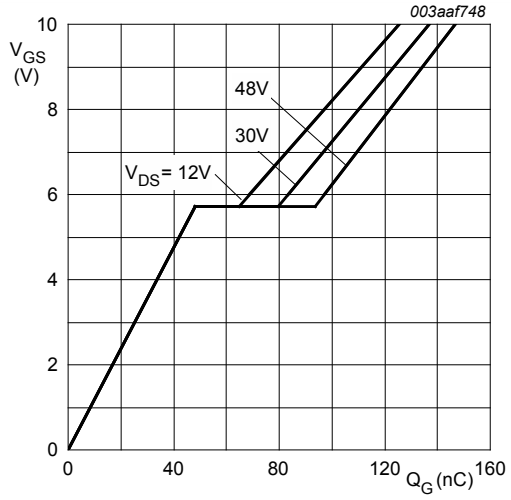


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25\ °C; I_D = 75\ A$

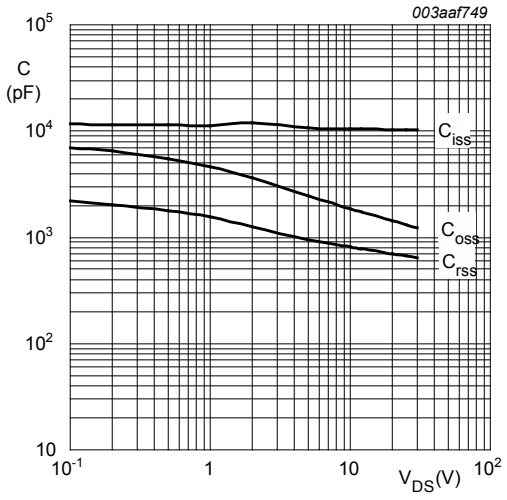


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\ V; f = 1\ MHz$

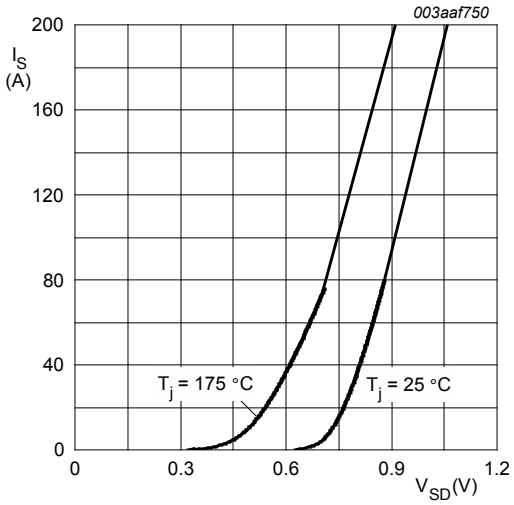
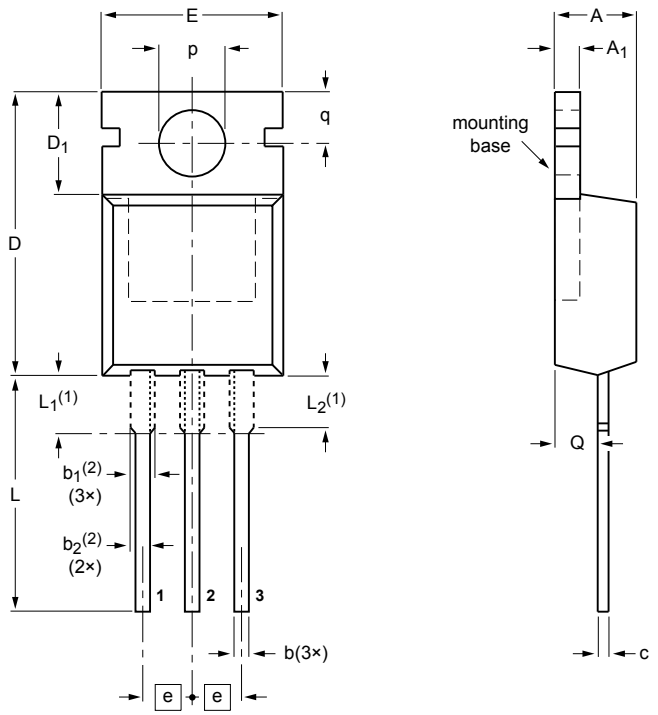


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0\ V$

10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1(2)	b_2(2)	c	D	D_1	E	e	L	L_1(1)	L_2(1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig. 18. Package outline TO-220AB (SOT78)

11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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12. Contents

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